USN

Sixth Semester B.E. Degree Examination, Dec.2013/Jan.2014 Microelectronics Circuits

Time: 3 hrs.

Max. Marks:100

Note: 1. Answer FIVE full questions, selecting at least TWO questions from each part.
2. State all assumptions, including missing data.

PART - A

- a. Derive an expression for drain-to-source current i_{DS} from i_D v/s V_{DS} relationship for triode and saturation regions of n-MOSFET. (10 Marks)
 - b. For an 0.8 μ m technology for which $t_{OX} = 15$ nm, $\mu_n = 550$ cm²/V. Find k'_n and c_{OX} and the overdrive voltage $V_{OX} = V_{as} V_1$ required to operate a transistor having W/L = 20 in saturation with $I_D = 0.2$ mA. What is the minimum V_{DS} needed? (06 Marks)
 - c. Design the circuit shown in Fig.Q.1(c) to obtain a drain voltage of 0.1V. What is the effective resistance between drain and source? At this operating point, let $V_t = 0.8V$ and

 $K_n^1 \left(\frac{W}{L} \right) = \text{Im} A / V^2. \tag{04 Marks}$

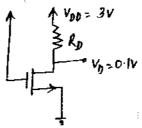


Fig.Q.1(c)

- 2 a. Briefly explain any two types of biasing methods in MOS amplifier circuits. (06 Marks)
 - b. For a common source amplifier with $g_m = 2$ mA/V, $r_0 = 50$ K Ω and $R_D = 10$ K Ω . $R_G = 10$ M Ω , $R_L = 20$ K Ω and $R_{sig} = 0.5$ M Ω . Calculate R_{in} , G_v , A_v , A_{vo} , R_{out} . (10 Marks)
 - c. Mention any 4 comparison of important characteristics of MOSFET and the BJT. (04 Marks)
- a. Explain the CMOS implementation of IC common source amplifier and hence explain how to determine its small signal voltage gain.
 - b. For the common gate amplifier with W/L = 4 μ m/0.2 μ m, μ_n C_{OX} = 350 μ A/V², r_0 = 18 KΩ, I_D = 100 μ A, g_m = 1.2 mA/V, χ = 0.2, R_s = 10KΩ, R_L = 100 KΩ, R_S = 20fF, R_S = 5fF, Find A_{vo}, R_S , $R_$
- 4 a. Explain the circuit of MOS cascade amplifier and hence obtain an expression for short circuit transconductance G_M. (10 Marks)
 - b. Explain briefly with neat circuit diagrams:
 - i) Wilson MOS mirror
 - (ii) Widlar current source.

(10 Marks)

PART - B

'5 a. Explain the basic operation of BJT differential pair.

(08 Marks)

- b. For the nMOS differential pair with a common-mode voltage V_{cm} applied as shown in Fig.Q.5(b), let $V_{DD} = V_{SS} = 2.5V$, $K'_n W/L = 3mA/V^2$, $V_{tn} = 0.7V$, I = 0.2mA, $R_D = 5K\Omega$. Neglect channel length modulation.
 - i) Find V_{OV} and V_{GS} for each transistor.
 - ii) For $V_{CM} = 0$ find V_s , i_{D1} , i_{D2} , V_{D1} and V_{D2} .
 - iii) Repeat (ii) for $V_{cm} = 1V$.
 - iv) What is the highest value of V_{cm} for which Q_1 and Q_2 remain in saturation, if current source I requires a minimum voltage of 0.3V to operate properly. What is the lowest value for V_{cm} . (12 Marks)

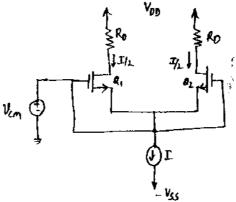


Fig.Q.5(b).

6 a. Explain briefly with expressions the properties of negative feedback.

(08 Marks)

b. A series-shunt feedback amplifier employs a basic amplifier with input and output resistances each of $1K\Omega$ and gain $\Lambda=2000$ V/V. The feedback factor $\beta=0.1$ V/V. Find the gain A_f the input resistance R_{i_f} and output resistance R_{o_f} of the closed loop amplifier.

(06 Marks)

c. Explain briefly an alternative approach for finding loop gain Aβ.

(06 Marks)

7 a. Explain instrumentation amplifier with neat circuit diagrams.

b. With neat diagram, explain the sample and hold circuit using opamp.

(08 Marks) (07 Marks)

c. Derive an expression for an input resistance of the inverting amplifier taking into account the finite open loop gain A of the opamp shown in Fig.Q.7(c). (05 Marks)

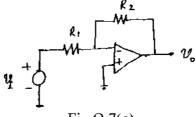


Fig.Q.7(c)

- 8 a. Briefly discuss the parameters used to characterize the operation and performance of logic circuit families. (08 Marks)
 - b. Write the expressions for propagation delay of an inverter.

(05 Marks)

c. Sketch a CMOS logic circuit that realizes the function $Y = AB + \overline{AB}$ using equivalence or co-incidence function. (07 Marks)

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